

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

F. Silicon and Group-IV Devices and Integration Technology 분과

Room G

봉래Ⅱ+Ⅲ(6층)

2016년 2월 24일(수) 08:30-10:00

[WG1-F] Materials and Processing Technologies

좌장

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| WG1-F-1 | 08:30-08:45 | High Density and Low Stress Titanium Nitride Metal Hard Mask (TiN MHM) by Physical Vapor Deposition (PVD) for 10nm Node and Beyond
Chang-Min Jeong, Eun-Kyoung Ma, Jouji Hiroishi, Shin Kim, Hyun-Ji Cho, Min-Soo Kim, Yong-Seok Jang, Byeong-Hwa Jeong, Ki-Young Yun, Seung-Su Choi, and In Sang Jeon
<i>Korea Institute for Super Materials, ULVAC Korea, Ltd.</i> |
| WG1-F-2 | 08:45-09:00 | Reverse Current Improvement of Metal/n-Ge Contact with TiO₂ Interlayer and Plasma Pre-Oxidation
Gwang-Sik Kim and Hyun-Yong Yu
<i>School of Electrical Engineering, Korea University</i> |
| WG1-F-3 | 09:00-09:15 | First-principle Study of GeSn Alloys for Electrical and Optical Characterizations
Yongbeom Cho ¹ , Oleg Rubel ² , and Seongjae Cho ^{1,3}
¹ Department of Electronic Engineering, Gachon University,
² Department of Materials Science and Engineering, McMaster University, ³ Graduate School of IT Convergence Engineering, Gachon University |
| WG1-F-4 | 09:15-09:30 | Improved Electrical Characteristics of FD-SOI Tunneling FET (TFET) Processed with Direct and Remote Interfacial Layer Scavenging Approaches
Donghwan Lim, Hoon Hee Han, Young Jin Kim, and Changhwan Choi
<i>Division of Materials Science and Engineering, Hanyang University</i> |
| WG1-F-5 | 09:30-09:45 | 고성능 트랜지스터를 위한 실리콘 나노멤브레인의 밸리 엔지니어링
김승윤 ¹ , 최성윤 ¹ , 황완식 ² , 조병진 ¹
¹ 한국과학기술원 전기및전자공학과, ² 한국 항공대학교 항공재료공학과 |
| WG1-F-6 | 09:45:10:00 | Growth of Polycrystalline Ge on Si by using Low-temperature Processes
Jeongmin Lee ¹ , Jungmin Lee ² , Mina Yun ³ , Yong-Hee Lee ² , and Seongjae Cho ^{1,3}
¹ Graduate School of IT Convergence Engineering, Gachon University,
² Department of Physics, KAIST, ³ Department of Electronic Engineering, Gachon University |